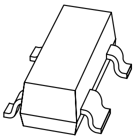


BCV62

PNP general-purpose double transistors

Rev. 4 — 26 July 2010

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		NPN complement
	NXP	JEITA	
BCV62	SOT143B	-	BCV61
BCV62A			BCV61A
BCV62B			BCV61B
BCV62C			BCV61C

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

1.4 Quick reference data

Table 2. Quick reference data

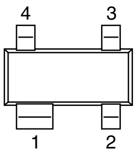
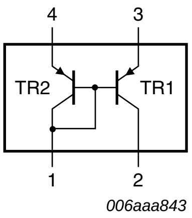
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	–30	V
I_C	collector current		-	-	–100	mA
Transistor TR1						
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –100 μA	100	-	-	
		V_{CE} = –5 V; I_C = –2 mA	100	-	800	

Table 2. Quick reference data *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor TR2						
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –2 mA				
	BCV62		100	-	800	
	BCV62A		100	-	250	
	BCV62B		220	-	475	
	BCV62C		420	-	800	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2		
2	collector TR1		
3	emitter TR1		
4	emitter TR2		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BCV62	-	plastic surface-mounted package; 4 leads	SOT143B
BCV62A			
BCV62B			
BCV62C			

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BCV62	3M*
BCV62A	3J*
BCV62B	3K*
BCV62C	3L*

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V_{CBO}	collector-base voltage	open emitter		-	–30	V
V_{CEO}	collector-emitter voltage	open base		-	–30	V
V_{EBS}	emitter-base voltage	$V_{CE} = 0$ V		-	–6	V
I_C	collector current			-	–100	mA
I_{CM}	peak collector current			-	–200	mA
I_{BM}	peak base current			-	–200	mA
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	250	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–65	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 8. Characteristics

$T_j = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor TR1						
I_{CBO}	collector-base cut-off current	$V_{CB} = -30$ V; $I_E = 0$ A	-	-	–15	nA
		$V_{CB} = -30$ V; $I_E = 0$ A; $T_j = 150$ °C	-	-	–5	µA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5$ V; $I_C = 0$ A	-	-	–100	nA
h_{FE}	DC current gain	$V_{CE} = -5$ V; $I_C = -100$ µA	100	-	-	
		$V_{CE} = -5$ V; $I_C = -2$ mA	100	-	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10$ mA; $I_B = -0.5$ mA	-	–75	–300	mV
		$I_C = -100$ mA; $I_B = -5$ mA	-	–250	–650	mV

Table 8. Characteristics *...continued*

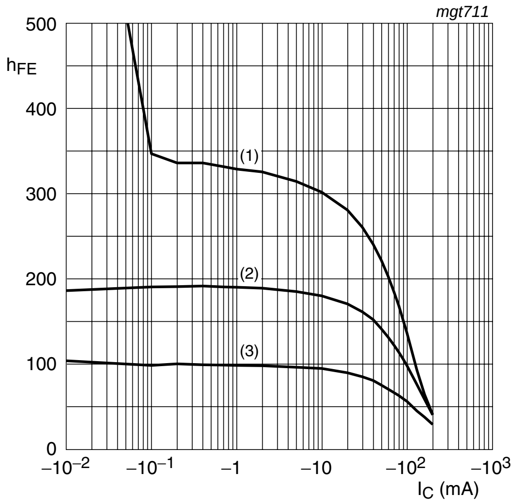
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{BEsat}	base-emitter saturation voltage	$I_C = -10$ mA; $I_B = -0.5$ mA	[1]	-	–700	-	mV
		$I_C = -100$ mA; $I_B = -5$ mA	[1]	-	–850	-	mV
V_{BE}	base-emitter voltage	$I_C = -2$ mA; $V_{CE} = -5$ V	[2]	–600	–650	–750	mV
		$I_C = -10$ mA; $V_{CE} = -5$ V	[2]	-	-	–820	mV
f_T	transition frequency	$V_{CE} = -5$ V; $I_C = -10$ mA; f = 100 MHz		100	-	-	MHz
C_c	collector capacitance	$V_{CB} = -10$ V; $I_E = i_e = 0$ A		-	4.5	-	pF
NF	noise figure	$V_{CE} = -5$ V; $I_C = -200$ µA; $R_S = 2$ kΩ; f = 1 kHz; B = 200 Hz		-	-	10	dB
Transistor TR2							
V_{EBS}	emitter-base voltage	$V_{CB} = 0$ V; $I_E = -250$ mA		-	-	–1.5	V
		$V_{CB} = 0$ V; $I_E = -10$ µA		–400	-	-	mV
h_{FE}	DC current gain	$V_{CE} = -5$ V; $I_C = -2$ mA					
	BCV62			100	-	800	
	BCV62A			100	-	250	
	BCV62B			220	-	475	
	BCV62C			420	-	800	
Transistors TR1 and TR2							
I_{C1}/I_{E2}	current matching	$I_{E2} = -0.5$ mA; $V_{CE1} = -5$ V;					
		$T_{amb} \leq 25$ °C		0.7	-	1.3	
		$T_{amb} \leq 150$ °C		0.7	-	1.3	
I_{E2}	emitter current 2	$V_{CE1} = -5$ V	[3]	-	-	–5	mA

[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

[3] Device, without emitter resistors, mounted on an FR4 PCB.



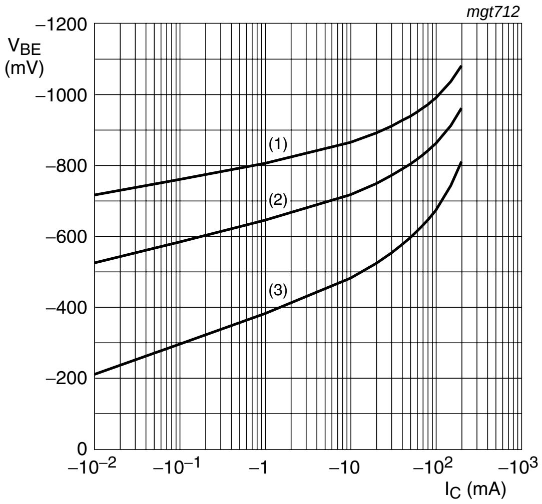
V_{CE} = –5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –55 °C

Fig 1. **BCV62A: DC current gain as a function of collector current; typical values**



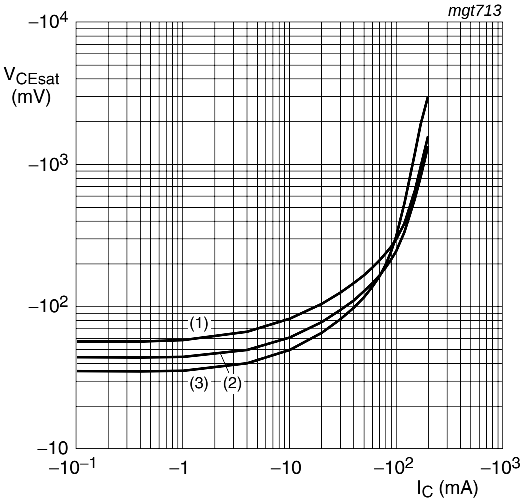
V_{CE} = –5 V

(1) T_{amb} = –55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 2. **BCV62A: Base-emitter voltage as a function of collector current; typical values**



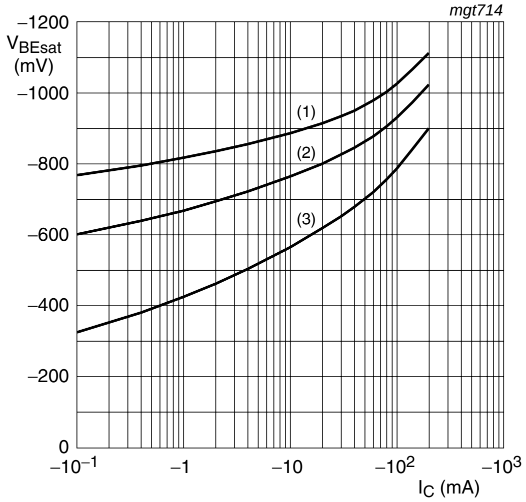
I_C/I_B = 20

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –55 °C

Fig 3. **BCV62A: Collector-emitter saturation voltage as a function of collector current; typical values**



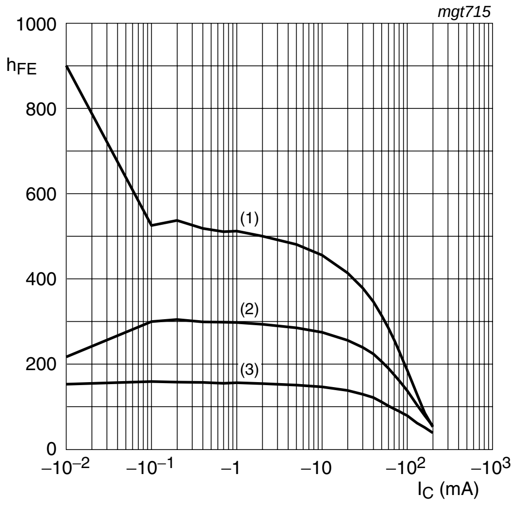
I_C/I_B = 20

(1) T_{amb} = –55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 4. **BCV62A: Base-emitter saturation voltage as a function of collector current; typical values**



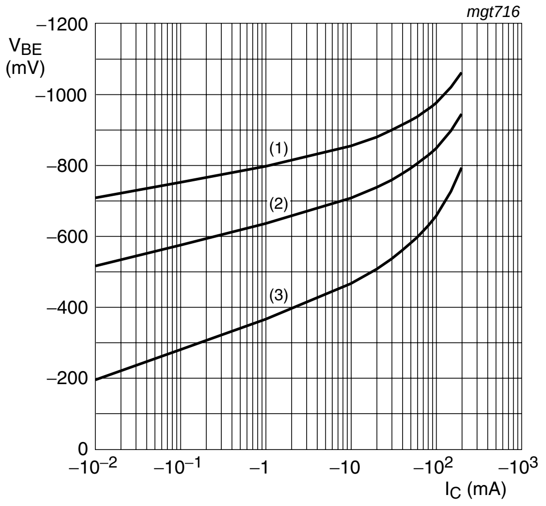
$V_{CE} = -5$ V

(1) $T_{amb} = 150$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 5. BCV62B: DC current gain as a function of collector current; typical values



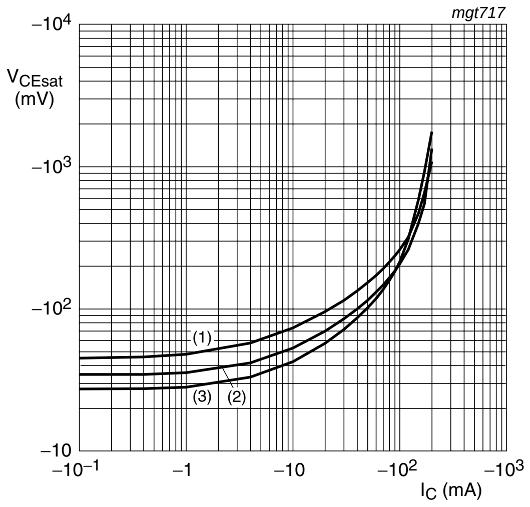
$V_{CE} = -5$ V

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 150$ °C

Fig 6. BCV62B: Base-emitter voltage as a function of collector current; typical values



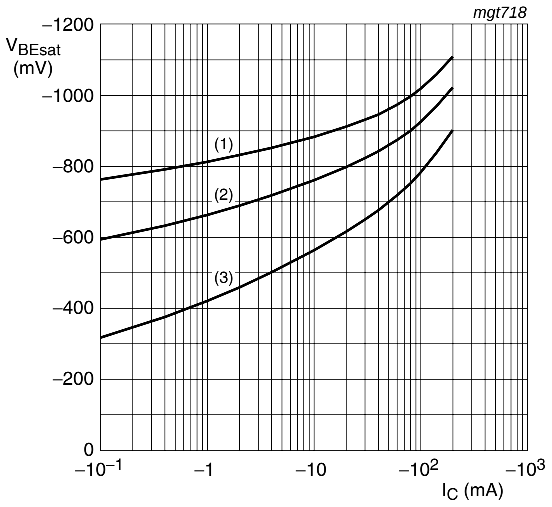
$I_C/I_B = 20$

(1) $T_{amb} = 150$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 7. BCV62B: Collector-emitter saturation voltage as a function of collector current; typical values



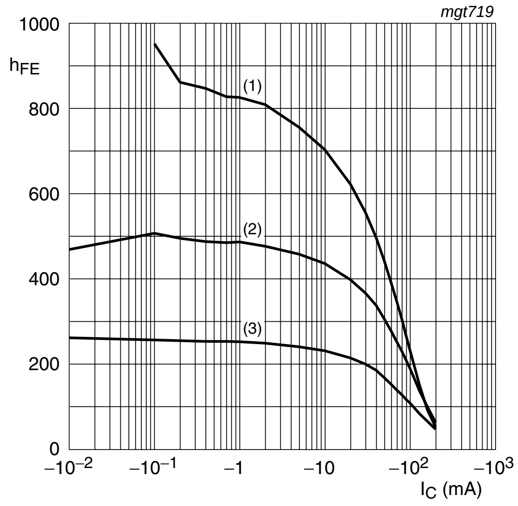
$I_C/I_B = 20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 150$ °C

Fig 8. BCV62B: Base-emitter saturation voltage as a function of collector current; typical values



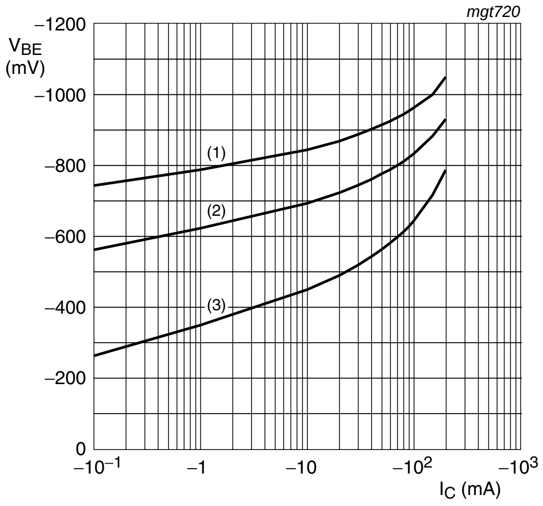
$V_{CE} = -5$ V

(1) $T_{amb} = 150$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 9. BCV62C: DC current gain as a function of collector current; typical values



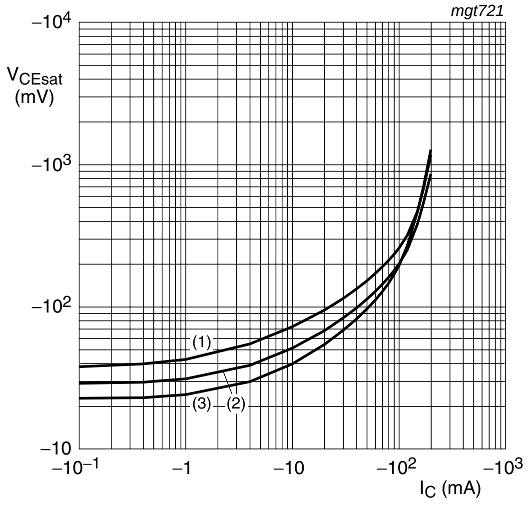
$V_{CE} = -5$ V

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 150$ °C

Fig 10. BCV62C: Base-emitter voltage as a function of collector current; typical values



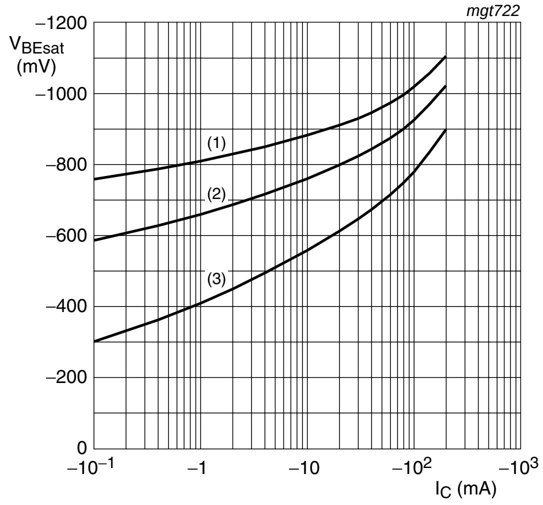
$I_C/I_B = 20$

(1) $T_{amb} = 150$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 11. BCV62C: Collector-emitter saturation voltage as a function of collector current; typical values



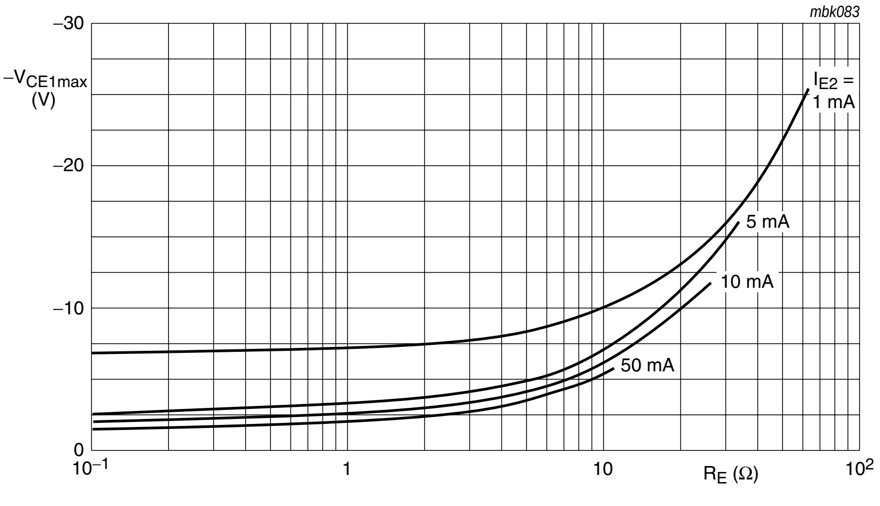
$I_C/I_B = 20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 150$ °C

Fig 12. BCV62C: Base-emitter saturation voltage as a function of collector current; typical values



$I_{C1}/I_{E2} = 1.3$

Fig 13. Maximum collector-emitter voltage as a function of emitter resistor (see Figure 15)

8. Test information

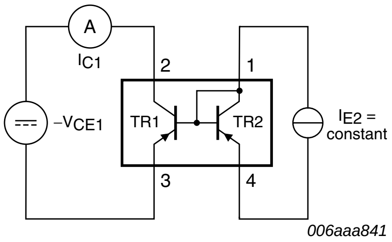


Fig 14. Test circuit current matching

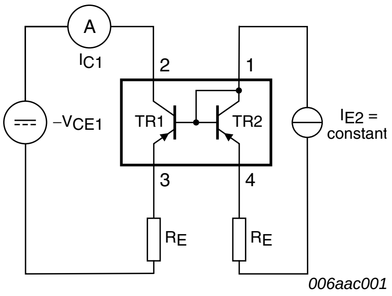


Fig 15. Current mirror with emitter resistors

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

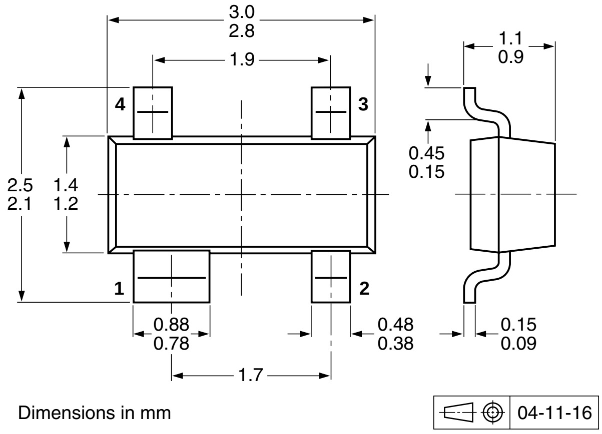


Fig 16. Package outline SOT143B

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BCV62	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235
BCV62A				
BCV62B				
BCV62C				

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

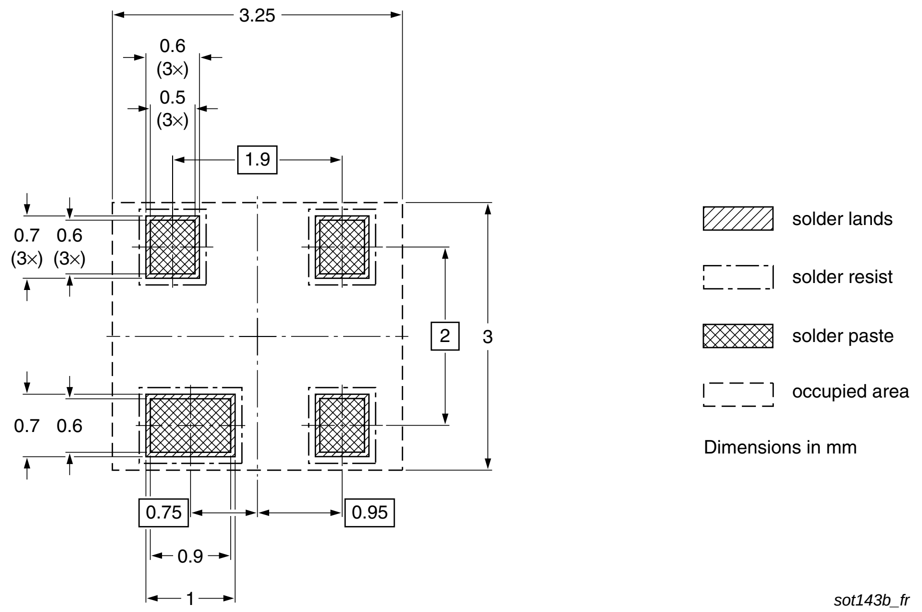


Fig 17. Reflow soldering footprint SOT143B

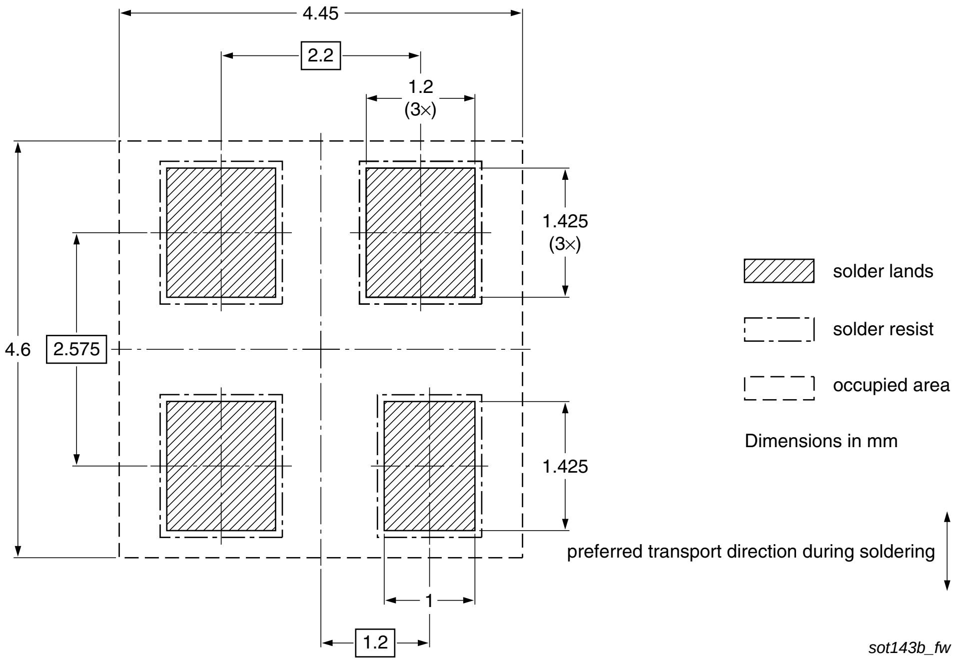


Fig 18. Wave soldering footprint SOT143B